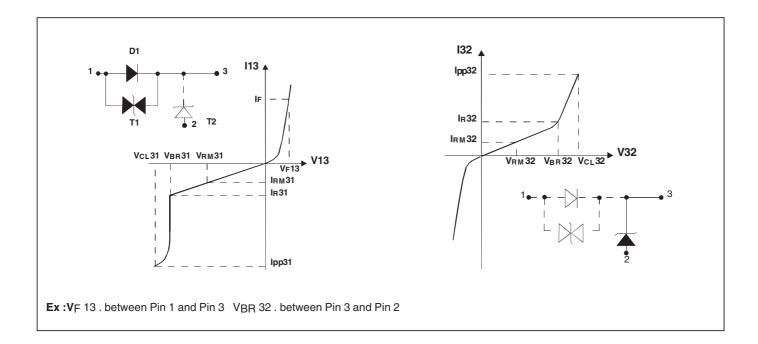
ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
I _{FSM}	Non repetitive surge peak forward current (Diode D1)	eak forward current tp = 10 ms		
lF	DC forward current (Diode D1)	Tc = 75°C	40	A
V _{PP}	Peak load dump voltage (see note 1and 2) 5 pulses (1 minute between each pulse)	80	V	
P _{PP}	Peak pulse power between Input and Output (Transil T1) Tj initial = 25°C	1500	W	
T _{stg} /Tj	Storage and operating junction temperature rang	- 40 to + 150	°C	
TL	Maximum lead temperature for soldering during at 4.5mm from case for TO220-AB	260	°C	

Note 1 : for a surge greater than the maximum value, the device will fail in short-circuit. Note 2 : see Load Dump curves.

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit	
Rth (j-c)	Junction to case	RBO40-40G RBO40-40T	1.0 1.0	°C/W
Rth (j-a)	Junction to ambient	RBO40-40T	60	°C/W



Symbol	Parameter	
V _{RM31} /V _{RM32}	Stand-off voltage Transil T1 / Transil T2.	
V _{BR31} /V _{BR32}	Breakdown voltage Transil T1 / Transil T2.	
I _{R31} /I _{R32}	Leakage current Transil T1 / Transil T2.	
V _{CL31} /V _{CL32}	Clamping voltage Transil T1 / Transil T2.	
V _{F13}	Forward voltage drop Diode D1.	
I _{PP}	Peak pulse current.	
αΤ	Temperature coefficient of V _{BR} .	
C ₃₁ /C ₃₂	Capacitance Transil T1 / Transil T2.	
C ₁₃	Capacitance of Diode D1	

ELECTRICAL CHARACTERISTICS : DIODE D1 (- 40°C < T_{amb} < + 85°C)

Cymhol	Symbol Test Conditions		Unit		
Symbol		Min.	Тур.	Max.	Unit
V _{F 13}	$I_F = 40 \text{ A}$			1.9	V
V _{F 13}	I _F = 20A			1.45	V
V _{F 13}	$I_F = 1 A$			1	V
V _{F 13}	I _F = 100 mA			0.95	V
C ₁₃	$F = 1MHz$ $V_R = 0 V$		3000		pF

ELECTRICAL CHARACTERISTICS : TRANSIL T1 (- $40^{\circ}C < T_{amb} < + 85^{\circ}C$)

Symbol	Test Conditions			Value		
Symbol				Тур.	Max.	Unit
V _{BR 31}	$I_{\rm R} = 1 \rm mA$				35	V
V _{BR 31}	$I_R = 1 \text{ mA}, T_{amb} = 25^{\circ}C$		24		32	V
I _{RM 31}	V _{RM} = 20 V				100	μA
I _{RM 31}	$V_{RM} = 20 \text{ V}, \text{ T}_{amb} = 25^{\circ}\text{C}$				10	μA
V _{CL 31}	I _{PP} = 37.5A, Tj initial = 25°C 10/1000μs				40	V
αΤ	Temperature coefficient of VBR				9	10 ⁻⁴ /°C
C 31	$F = 1MHz$ $V_R = 0 V$			3000		pF

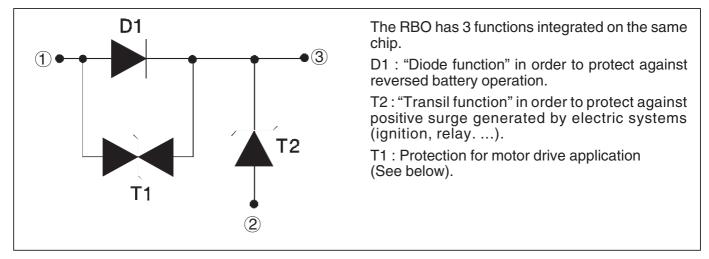
ELECTRICAL CHARACTERISTICS : TRANSIL T2 (- $40^{\circ}C < T_{amb} < + 85^{\circ}C$)

Symbol	Test Conditions		Unit		
Symbol		Min.	Тур.	Max.	Unit
V _{BR 32}	$I_{R} = 1 \text{ mA}$	22		35	V
V _{BR 32}	$I_R = 1 \text{ mA}, T_{amb} = 25^{\circ}C$	24		32	V
I _{RM 32}	V _{RM} = 20 V			100	μA
I _{RM 32}	$V_{RM} = 20 \text{ V}, \text{ T}_{amb} = 25^{\circ}\text{C}$			10	μA
V _{CL 32}	$I_{PP} = 20 \text{ A} \text{ (note 1)}$			40	V
αΤ	Temperature coefficient of VBR			9	10 ⁻⁴ /°C
C ₃₂	$F = 1MHz$ $V_R = 0 V$		8000		pF

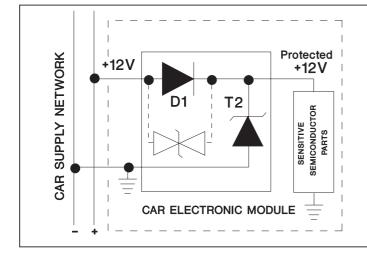
Note 1 : One pulse, see pulse definition in load dump test generator circuit.



PRODUCT DESCRIPTION



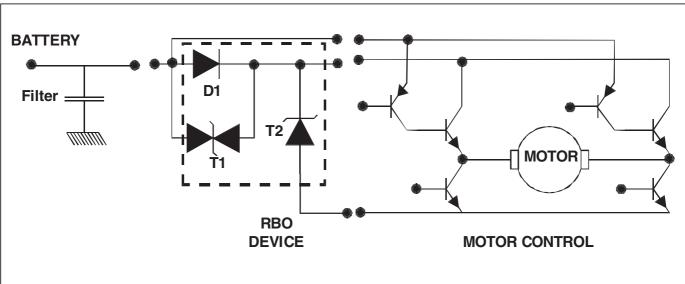
BASIC APPLICATION



* The monolithic multi-function protection (RBO) has been developed to protect sensitive semiconductors in car electronic modules against both overvoltage and battery reverse.

* In addition, the RBO circuit prevents overvoltages generated by the module from affecting the car supply network.

Δ7/



MOTOR DRIVER APPLICATION

In this application, one half of the motor drive circuit is supplied through the "RBO" and is thus protected as per its basic function application.

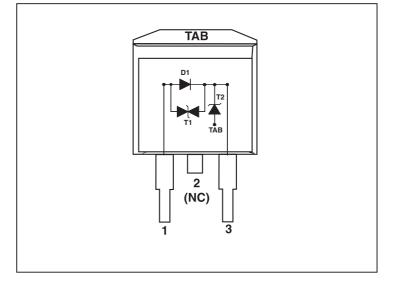
The second part is connected directly to the "car supply network" and is protected as follows :

- For positive surges : T2 (clamping phase) and D1 in forward-biased.
- For negative surges : T1 (clamping phase) and T2 in forward-biased.

4/10

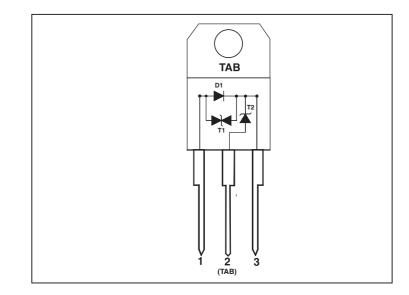
PINOUT configuration in D^2PAK:

- Input (1): Pin 1
- Output (3): Pin 3
- Gnd (2): Connected to base Tab
- Marking : Logo, date code, RBO40-40G



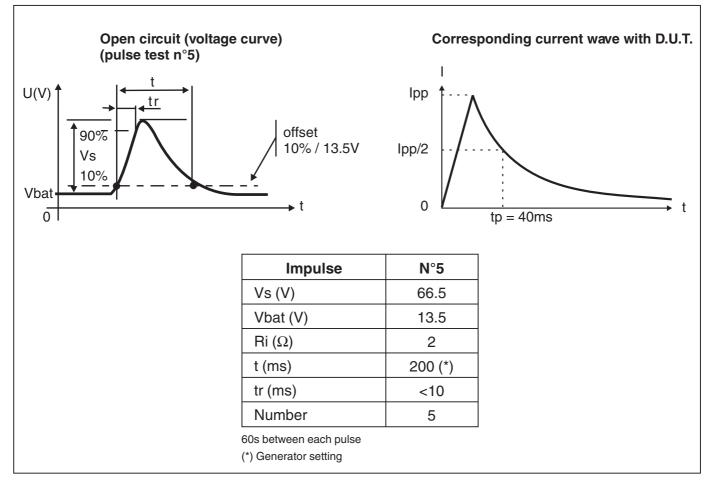
PINOUT configuration in TO220AB :

- Input (1): Pin 1
- Output (3): Pin 3
- GND (2): Connected to base Tab
- Marking : Logo, date code, RBO40-40T

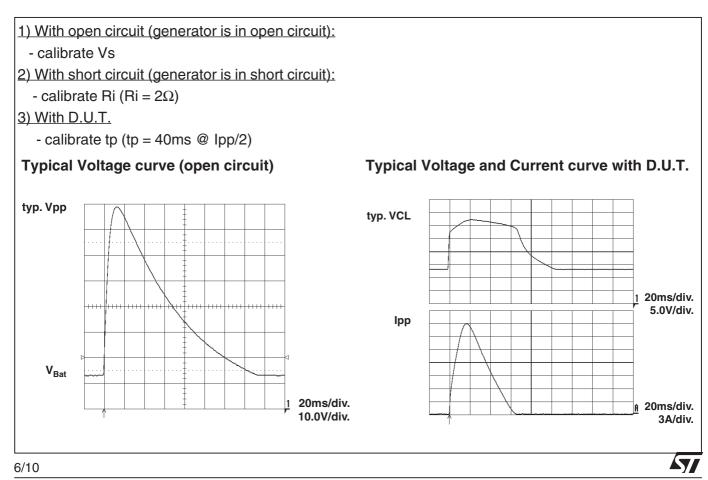


RBO40-40G / RBO40-40T

LOAD DUMP TEST GENERATOR CIRCUIT (SCHAFFNER NSG 506 C). Issued from ISO / DTR 7637.



CALIBRATION METHOD FOR SCHAFFNER NSG 506 C



Downloaded from Arrow.com.

Fig. 1 : Peak pulse power versus exponential pulse duration (Tj initial = 85° C).

Fig. 2-1 : Clamping voltage versus peak pulse current (Tj initial = 85°C).

Exponential waveform tp = 40 ms and tp = 1 ms (TRANSIL T2).

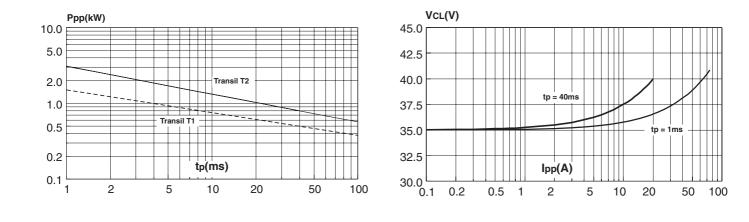


Fig. 2-2 : Clamping voltage versus peak pulse current (Tj initial = 85°C).

Exponential waveform tp = 1 ms and tp = 20 μs (TRANSIL T1).

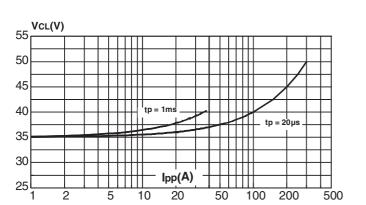


Fig. 3 : Relative variation of peak pulse power versus junction temperature.

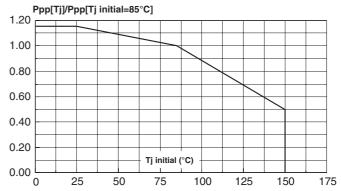
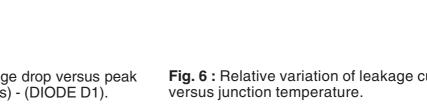
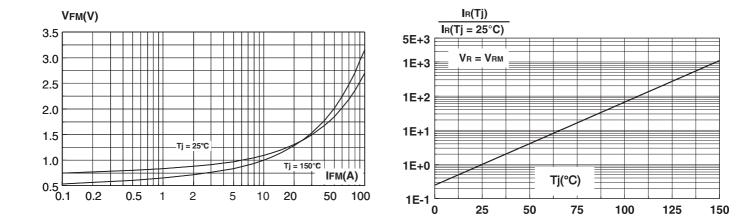


Fig. 4 : Relative variation of thermal impedance junction to case versus pulse duration.

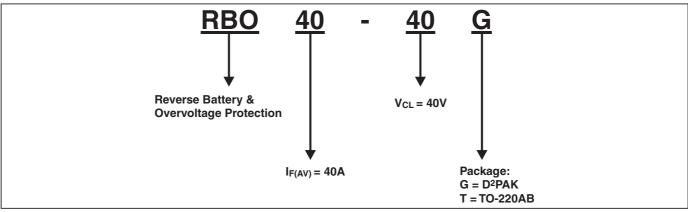
Fig. 5-2 : Peak forward voltage drop versus peak forward current (typical values) - (DIODE D1).

Fig. 6 : Relative variation of leakage current versus junction temperature.





ORDERING INFORMATION



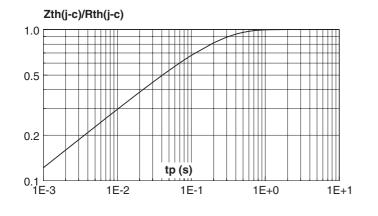
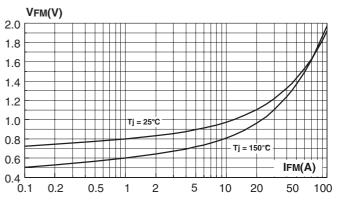


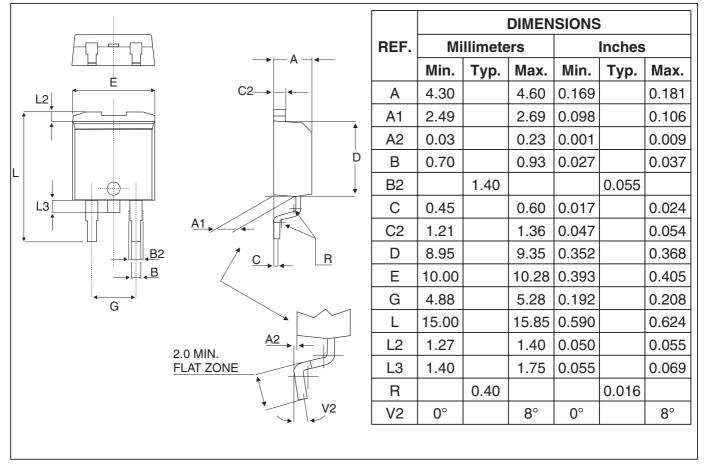
Fig. 5-1 : Peak forward voltage drop versus peak forward current (typical values) - (TRANSIL T2).



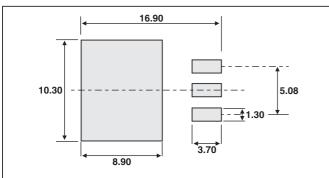
5

PACKAGE MECHANICAL DATA

D²PAK Plastic



FOOT-PRINT (in millimeters) D²PAK





PACKAGE MECHANICAL DATA TO-220AB Plastic

	REF.	Mi Min. 15.20	llimete Typ.	ers Max.		Inches	
		<u> </u>	Тур.	Max			
		15 20		IVIUX.	Min.	Тур.	Max.
		15.20		15.90	0.598		0.625
	a1		3.75			0.147	
	a2	13.00		14.00	0.511		0.551
	В	10.00		10.40	0.393		0.409
	b1	0.61		0.88	0.024		0.034
	b2	1.23		1.32	0.048		0.051
14	С	4.40		4.60	0.173		0.181
$\square \oplus \square \square \square \square \square \square \square \square $	c1	0.49		0.70	0.019		0.027
	c2	2.40		2.72	0.094		0.107
	е	2.40		2.70	0.094		0.106
	F	6.20		6.60	0.244		0.259
	1	3.75		3.85	0.147		0.151
	14	15.80	16.40	16.80	0.622	0.646	0.661
₩₩₩₩	L	2.65		2.95	0.104		0.116
	12	1.14		1.70	0.044		0.066
e c1	13	1.14		1.70	0.044		0.066
	Μ		2.60			0.102	

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics.

All other names are the property of their respective owners.

© 2005 STMicroelectronics - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany -Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain -

Sweden - Switzerland - United Kingdom - United States

www.st.com

47/

10/10